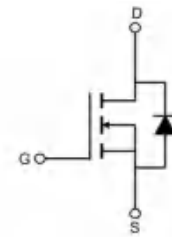


# AP30H60K

## N-Channel Enhancement Mosfet

### Feature

- 30V,50A  
 $R_{DS(ON)} < 7.5m\Omega @ V_{GS}=10V$       TYP:6.0m $\Omega$   
 $R_{DS(ON)} < 13m\Omega @ V_{GS}=4.5V$       TYP:9.5 m $\Omega$
- Advanced Trench Technology
- Lead free product is acquired
- Excellent  $R_{DS(ON)}$  and Low Gate Charge



Schematic Diagram



Marking and pin assignment

### Application

- PWM applications
- Load Switch
- Power management

### Package Marking and Ordering Information

| Device Marking | Device   | Device Package | Reel Size | Tape width | Quantity (PCS) |
|----------------|----------|----------------|-----------|------------|----------------|
| 30H60K         | AP30H60K | TO-252         | 13 inch   | -          | 2500           |

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

| Parameter   | Symbol          | Value     | Unit               |
|---|-----------------|-----------|--------------------|
| Drain-Source Voltage                                    | $V_{DS}$        | 30        | V                  |
| Gate-Source Voltage                                     | $V_{GS}$        | $\pm 20$  | V                  |
| Continuous Drain Current ( $T_a=25^\circ\text{C}$ )     | $I_D$           | 50        | A                  |
| Continuous Drain Current ( $T_a=100^\circ\text{C}$ )    | $I_D$           | 33        | A                  |
| Pulsed Drain Current <sup>(1)</sup>                     | $I_{DM}$        | 200       | A                  |
| Singel Pulsed Avalanche Energy <sup>(2)</sup>           | $E_{AS}$        | 36        | mJ                 |
| Power Dissipation                                       | $P_D$           | 33        | W                  |
| Thermal Resistance from Junction to Case <sup>(4)</sup> | $R_{\theta JC}$ | 3.8       | $^\circ\text{C/W}$ |
| Junction Temperature                                    | $T_J$           | 150       | $^\circ\text{C}$   |
| Storage Temperature                                     | $T_{STG}$       | -55~ +150 | $^\circ\text{C}$   |

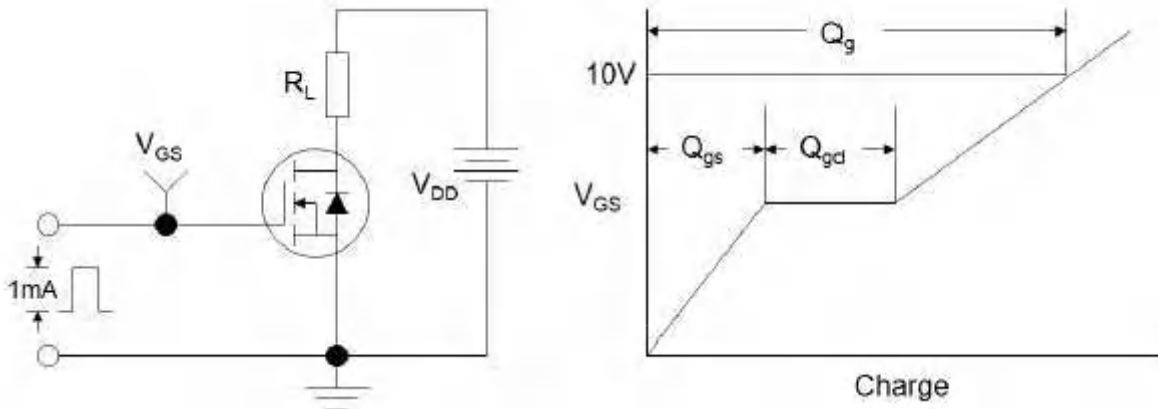
**MOSFET ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

| Parameter                                 | Symbol               | Test Condition   | Min | Type | Max  | Unit |
|---|----------------------|--|-----|------|------|------|
| <b>Static Characteristics</b>             |                      |  |     |      |      |      |
| Drain-source breakdown voltage            | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA  | 30  | -    | -    | V    |
| Zero gate voltage drain current           | I <sub>DSS</sub>     | V <sub>DS</sub> =30V, V <sub>GS</sub> = 0V   | -   | -    | 1    | μA   |
| Gate-body leakage current                 | I <sub>GSS</sub>     | V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V  | -   | -    | ±100 | nA   |
| Gate threshold voltage <sup>(3)</sup>     | V <sub>GS(th)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                               | 1   | 1.5  | 2.5  | V    |
| Drain-source on-resistance <sup>(3)</sup> | R <sub>DS(on)</sub>  | V <sub>GS</sub> =10V, I <sub>D</sub> =30A  | -   | 6.0  | 7.5  | mΩ   |
|   |                      | V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A   | -   | 9.5  | 13   |      |
| <b>Dynamic characteristics</b>            |                      |  |     |      |      |      |
| Input Capacitance                         | C <sub>iss</sub>     | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f =1MHz                                     | -   | 1140 | -    | pF   |
| Output Capacitance                        | C <sub>oss</sub>     |  | -   | 175  | -    |      |
| Reverse Transfer Capacitance              | C <sub>rss</sub>     |  | -   | 151  | -    |      |
| <b>Switching characteristics</b>          |                      |  |     |      |      |      |
| Turn-on delay time                        | t <sub>d(on)</sub>   | V <sub>DD</sub> =15V, I <sub>D</sub> =25A,<br>V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω | -   | 15   | -    | ns   |
| Turn-on rise time                         | t <sub>r</sub>       |  | -   | 19   | -    |      |
| Turn-off delay time                       | t <sub>d(off)</sub>  |  | -   | 35   | -    |      |
| Turn-off fall time                        | t <sub>f</sub>       |  | -   | 21   | -    |      |
| Total Gate Charge                         | Q <sub>g</sub>       | V <sub>DS</sub> =15V, I <sub>D</sub> =25A,<br>V <sub>GS</sub> =10V                     | -   | 13.3 | -    | nC   |
| Gate-Source Charge                        | Q <sub>gs</sub>      |  | -   | 3.1  | -    |      |
| Gate-Drain Charge                         | Q <sub>gd</sub>      |  | -   | 5    | -    |      |
| Reverse Recovery Charge                   | Q <sub>rr</sub>      | I <sub>F</sub> =30A, di/dt=100A/us   |     | 26   |      | nC   |
| Reverse Recovery Time                     | T <sub>rr</sub>      | I <sub>F</sub> =30A, di/dt=100A/us   |     | 25   |      | ns   |
| <b>Source-Drain Diode characteristics</b> |                      |  |     |      |      |      |
| Diode Forward voltage <sup>(3)</sup>      | V <sub>DS</sub>      | V <sub>GS</sub> =0V, I <sub>S</sub> =25A   | -   | -    | 1.2  | V    |
| Diode Forward current <sup>(4)</sup>      | I <sub>S</sub>       |  | -   | -    | 50   | A    |

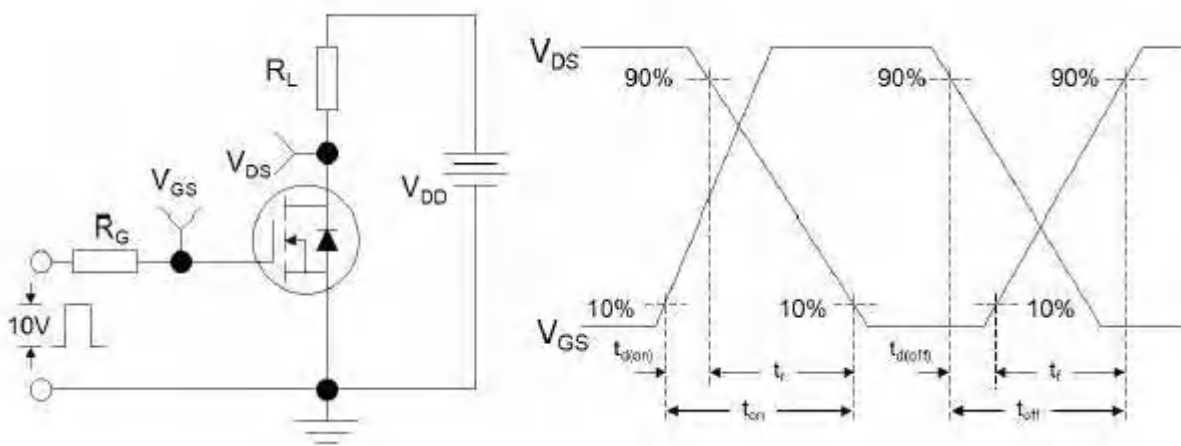
**Notes:**

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=15V, R<sub>G</sub>=25 Ω, L=0.5mH
3. Pulse Test: pulse width≤300μs, duty cycle≤2%
4. Surface Mounted on FR4 Board, t≤10 sec

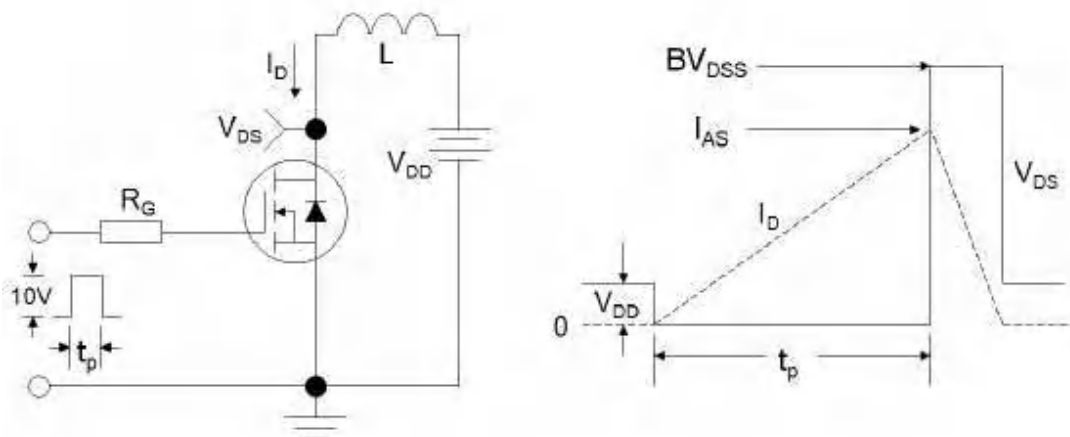
**Test Circuit**



**Figure1:Gate Charge Test Circuit & Waveform**



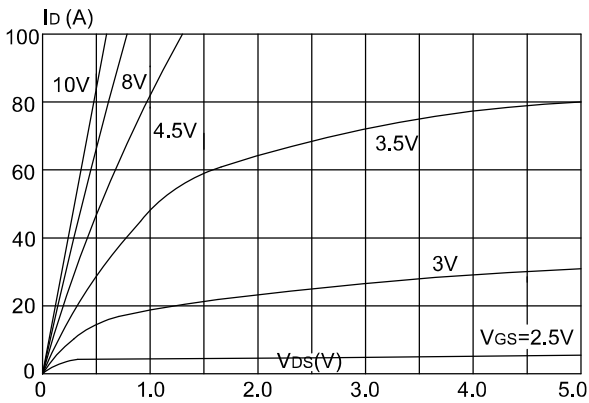
**Figure 2: Resistive Switching Test Circuit & Waveforms**



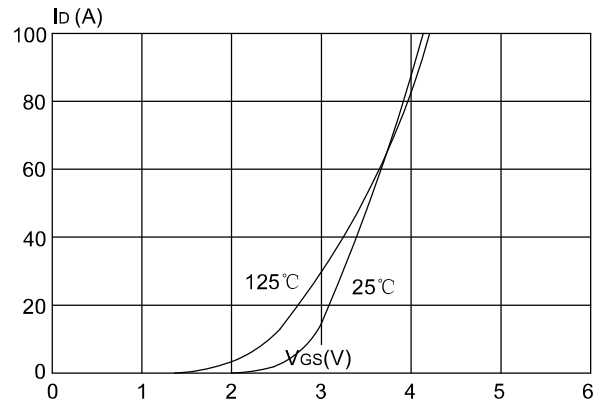
**Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms**

**Typical Performance Characteristics**

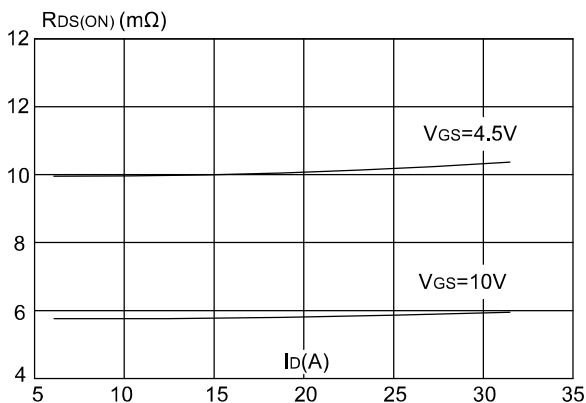
**Figure 1: Output Characteristics**



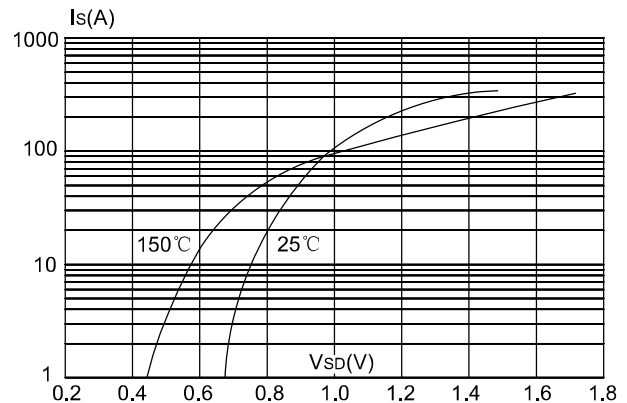
**Figure 2: Typical Transfer Characteristics**



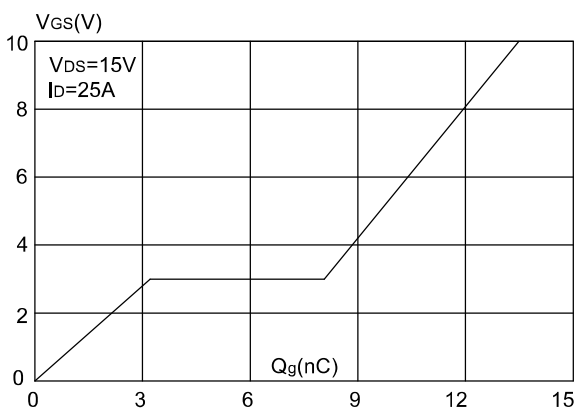
**Figure 3: On-resistance vs. Drain Current**



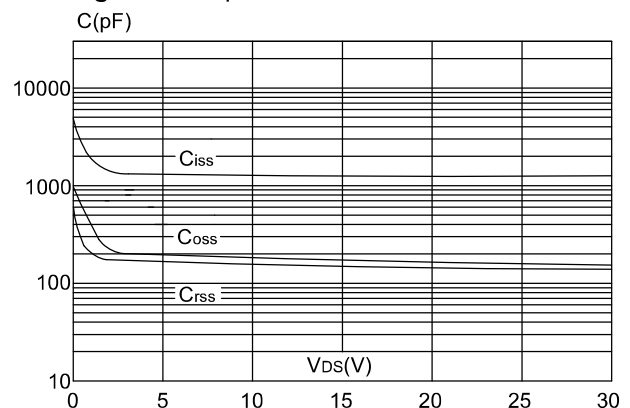
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**



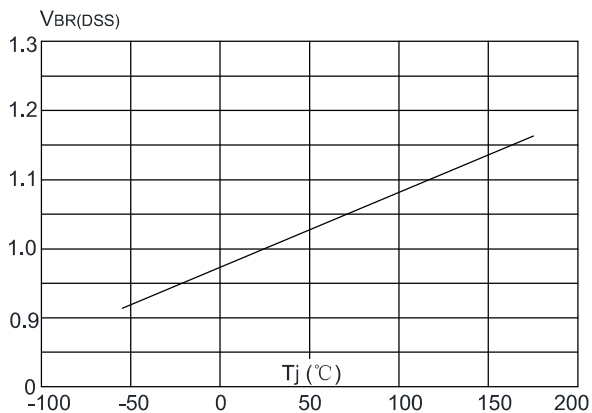
**Figure 6: Capacitance Characteristics**



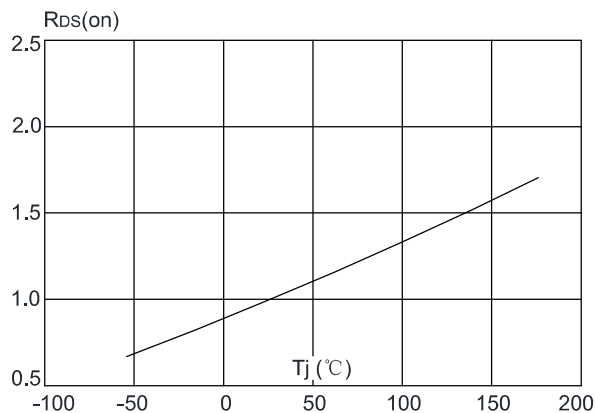
# AP30H60K

## N-Channel Enhancement Mosfet

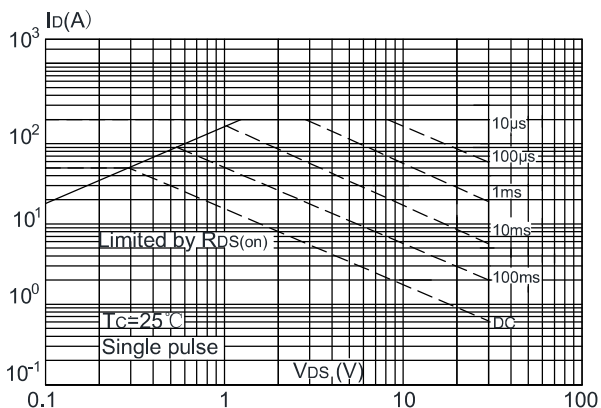
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



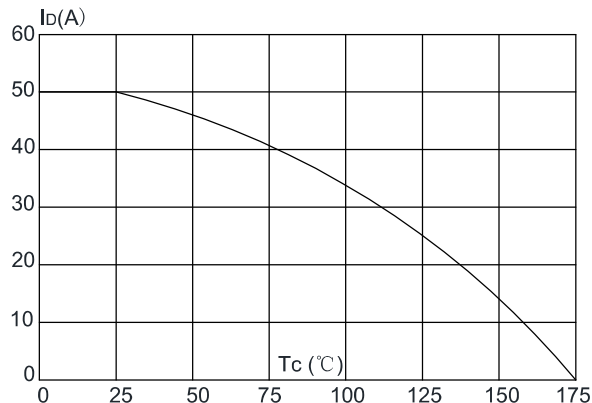
**Figure 8:** Normalized on Resistance vs. Junction Temperature



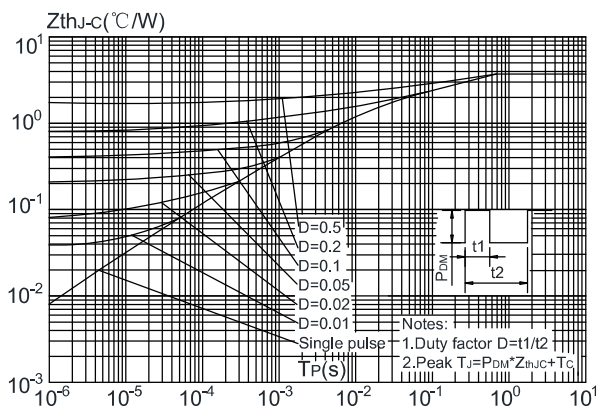
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



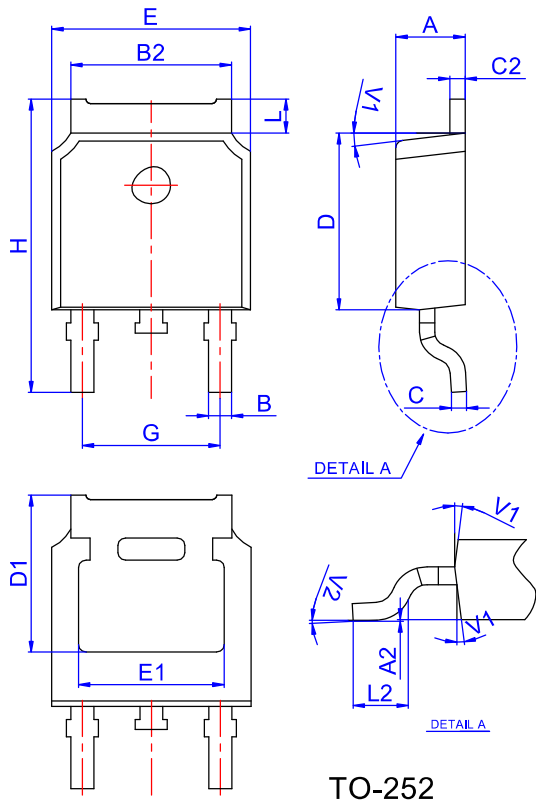
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



# AP30H60K

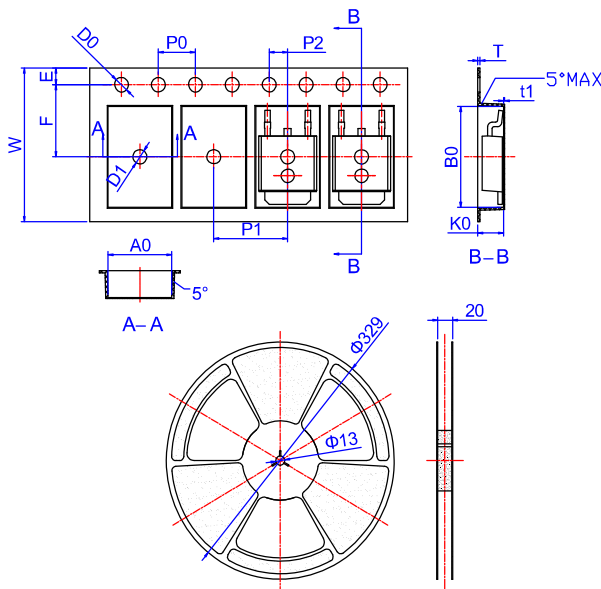
## N-Channel Enhancement Mosfet

### TO-252 Package Information



| Ref. | Dimensions  |      |       |          |      |       |
|------|-------------|------|-------|----------|------|-------|
|      | Millimeters |      |       | Inches   |      |       |
|      | Min.        | Typ. | Max.  | Min.     | Typ. | Max.  |
| A    | 2.10        |      | 2.50  | 0.083    |      | 0.098 |
| A2   | 0           |      | 0.10  | 0        |      | 0.004 |
| B    | 0.66        |      | 0.86  | 0.026    |      | 0.034 |
| B2   | 5.18        |      | 5.48  | 0.202    |      | 0.216 |
| C    | 0.40        |      | 0.60  | 0.016    |      | 0.024 |
| C2   | 0.44        |      | 0.58  | 0.017    |      | 0.023 |
| D    | 5.90        |      | 6.30  | 0.232    |      | 0.248 |
| D1   | 5.30REF     |      |       | 0.209REF |      |       |
| E    | 6.40        |      | 6.80  | 0.252    |      | 0.268 |
| E1   | 4.63        |      |       | 0.182    |      |       |
| G    | 4.47        |      | 4.67  | 0.176    |      | 0.184 |
| H    | 9.50        |      | 10.70 | 0.374    |      | 0.421 |
| L    | 1.09        |      | 1.21  | 0.043    |      | 0.048 |
| L2   | 1.35        |      | 1.65  | 0.053    |      | 0.065 |
| V1   |             | 7°   |       |          | 7°   |       |
| V2   | 0°          |      | 6°    | 0°       |      | 6°    |

### Reel Specification-TO-252



| Ref. | Dimensions  |       |       |        |       |       |
|------|-------------|-------|-------|--------|-------|-------|
|      | Millimeters |       |       | Inches |       |       |
|      | Min.        | Typ.  | Max.  | Min.   | Typ.  | Max.  |
| W    | 15.90       | 16.00 | 16.10 | 0.626  | 0.630 | 0.634 |
| E    | 1.65        | 1.75  | 1.85  | 0.065  | 0.069 | 0.073 |
| F    | 7.40        | 7.50  | 7.60  | 0.291  | 0.295 | 0.299 |
| D0   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| D1   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| P0   | 3.90        | 4.00  | 4.10  | 0.154  | 0.157 | 0.161 |
| P1   | 7.90        | 8.00  | 8.10  | 0.311  | 0.315 | 0.319 |
| P2   | 1.90        | 2.00  | 2.10  | 0.075  | 0.079 | 0.083 |
| A0   | 6.85        | 6.90  | 7.00  | 0.270  | 0.271 | 0.276 |
| B0   | 10.45       | 10.50 | 10.60 | 0.411  | 0.413 | 0.417 |
| K0   | 2.68        | 2.78  | 2.88  | 0.105  | 0.109 | 0.113 |
| T    | 0.24        |       | 0.27  | 0.009  |       | 0.011 |
| t1   | 0.10        |       |       | 0.004  |       |       |
| 10P0 | 39.80       | 40.00 | 40.20 | 1.567  | 1.575 | 1.583 |